45V N-Channel Enhancement Mode MOSFET

Description

The PECN4575G uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge.It can be used in a wide variety of applications.

General Features

- V_{DS} =45V I_D =75A
  $R_{DS(ON)}$(Typ.)=6.2mΩ @V_{GS}=10V
  $R_{DS(ON)}$(Typ.)=7.2mΩ @V_{GS}=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

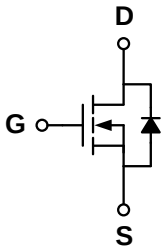
- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

Package

- TO-252-2L

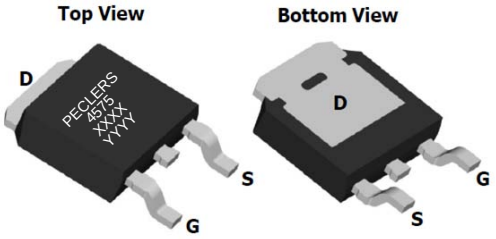
100% UIS TESTED!
100% ΔVds TESTED!

Schematic diagram



Marking and pin assignment

TO-252-2L
（Top View）



PECLERS 4575—Product Name
XXXX—Wafer Lot No.
YYYY—Quality Code

Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PECN4575G	-55°C to +150°C	TO-252-2L	2500

Absolute Maximum Ratings (TA=25℃ unless otherwise noted)

parameter		symbol	limit	unit
Drain-source voltage		V_{DS}	45	V
Gate-source voltage		V_{GS}	±20	V
Continuous Drain Current	TC=25°C	I_D	75	A
	TC=100°C		50	
Pulsed Drain Current		I_{DP}	300	A
Avalanche energy(L=0.5mH) (note1)		E_{AS}	200	mJ
Maximum power dissipation	TC=25°C	P_D	60	W
Operating junction Temperature range		Tj	-55—150	℃

Electrical Characteristics (TA=25℃ unless otherwise noted)

Parameter	Symbol	Condition		Min	Typ	Max	Unit
Static Characteristics							
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA		45	55	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=45V, V_{GS}=0V	T_J=25°C	-	-	1	μA
			T_J=85°C	-	-	5	
Gate Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V		-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA		1.00	1.50	2.00	V
Drain-source on-state resistance[1]	$R_{DS(ON)}$	V_{GS}=10V, I_D=75A		-	6.2	8	mΩ
		V_{GS}=4.5V, I_D=60A		-	7.2	9	
Forward Transconductance	$I_{D(ON)}$	V_{DS}=5V,I_D=20A		20	-	-	S
Diode Characteristics							
Diode Continuous Forward Current	I_S			-	-	12	A
Reverse Recovery Time	t_{rr}	I_F=40A, dI/dt=20A/us		-	29	-	ns
Reverse Recovery Charge	Q_{rr}			-	26	-	nC
Dynamic Characteristics[2]							
Input capacitance	C_{ISS}	V_{GS}=0V ,V_{DS}=22.5V f=1.0MHz		-	2600	-	pF
Output capacitance	C_{OSS}			-	241	-	
Reverse transfer capacitance	C_{RSS}			-	195	-	
Turn-on delay time	$t_{D(ON)}$	V_{GS}=10V, V_{DD}=22.5V, R_L=1Ω, R_G=2Ω		-	6.5	-	ns
Turn-on Rise time	tr			-	17	-	
Turn-off delay time	$t_{D(OFF)}$			-	29.5	-	
Turn-off Fall time	tf			-	17	-	
Total gate charge	Q_g	V_{GS}=10V,I_D=2A V_{DS}=10V		-	60		nC
Gate-source charge	Q_{gs}				6.1		
Gate-drain charge	Q_{gd}			-	12	-	
Drain-Source Diode Characteristics							
Diode forward voltage	V_{SD}	I_{SD}=10A,V_{GS}=0V		-	0.8	1.2	V

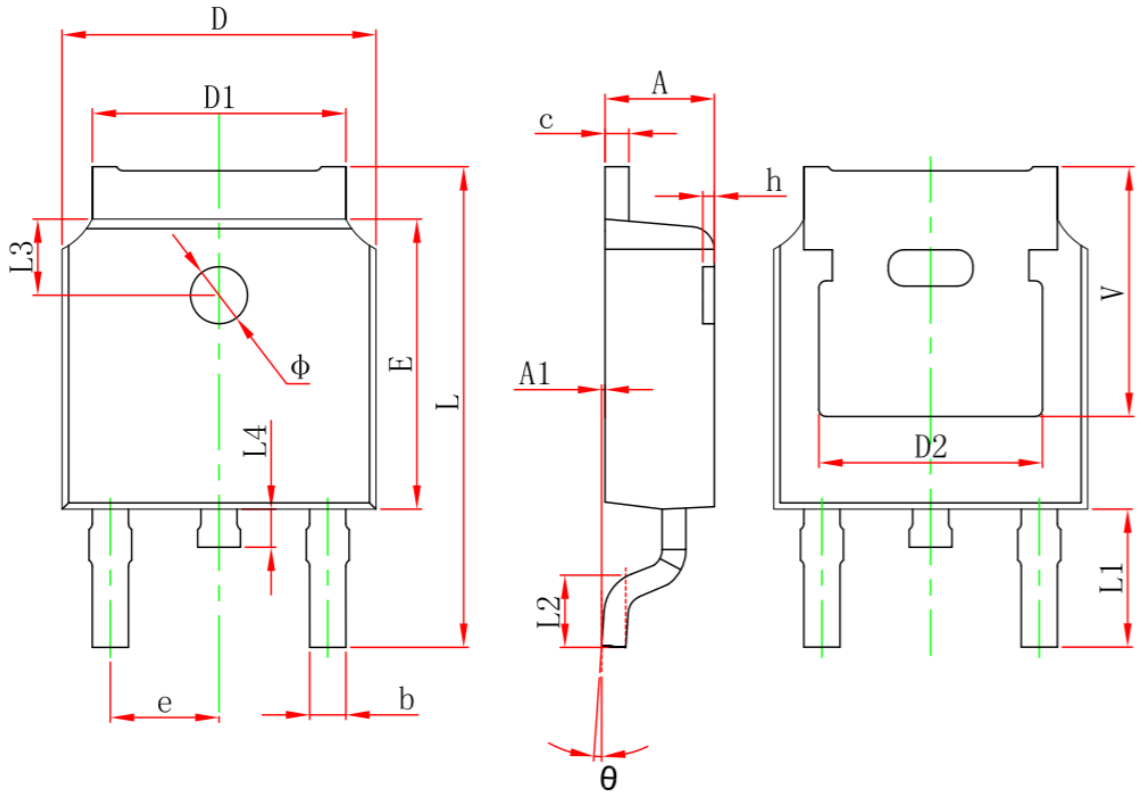
Note: 1：Eas test：V_{DD}=10V，R_G=25ohm，L=500uH

2：Pulse test; pulse width ≦ 300ns, duty cycle ≦ 2%.

3：Guaranteed by design, not subject to production testing.

Package Information

- **TO-252-2L**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	